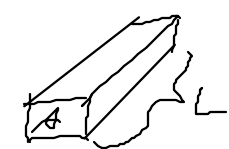
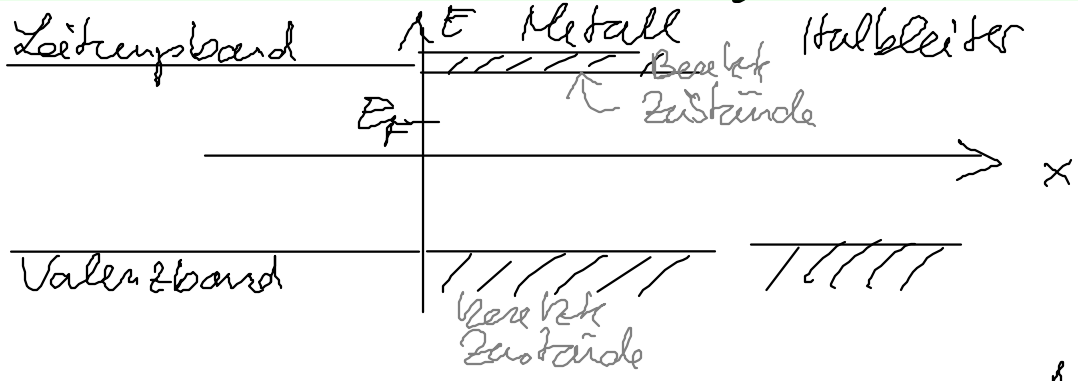


$L \rightarrow 0: \gamma \rightarrow \infty$

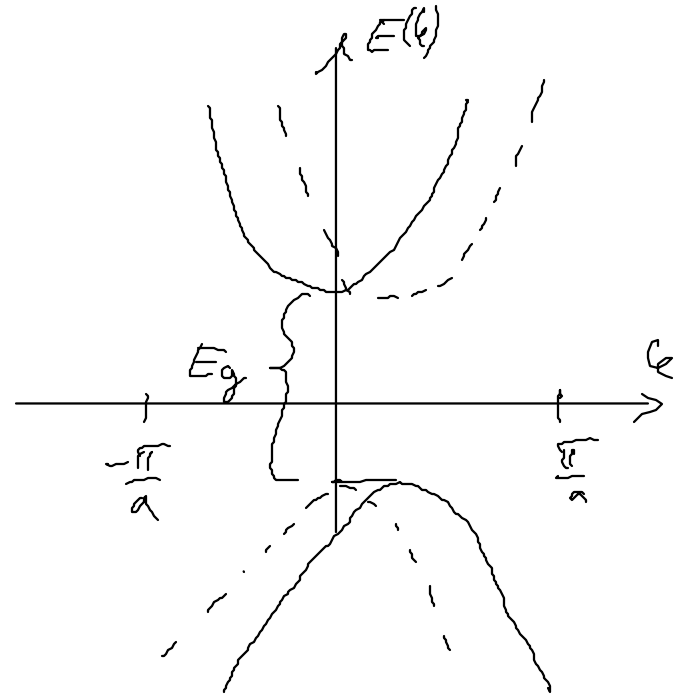


Leitwert $\gamma = \frac{\sigma A}{L}$

Modifikation der klassischen Physik in Nanostrukturen

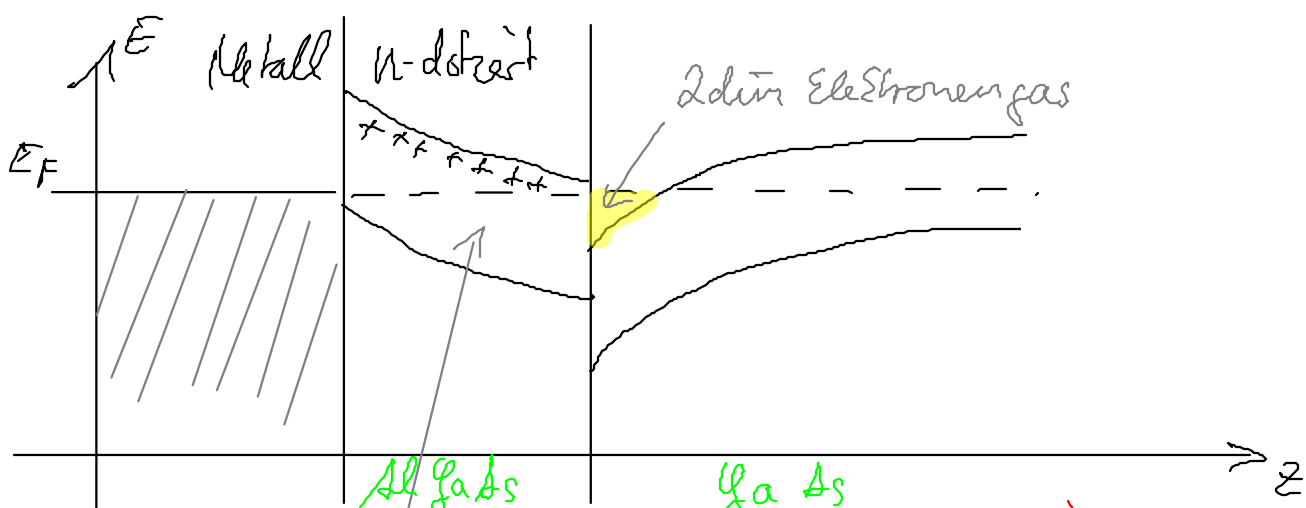


	GaAs	Si
$\frac{m}{m_e}$	0,067	0,19
λ_F	40 nm	100 nm
λ_{imp}	$10^2 - 10^4$ nm	≈ 100 nm
L_ϕ	$200 \text{ nm} \sqrt{\frac{h}{T}}$	$40 - 400 \text{ nm} \sqrt{\frac{h}{T}}$



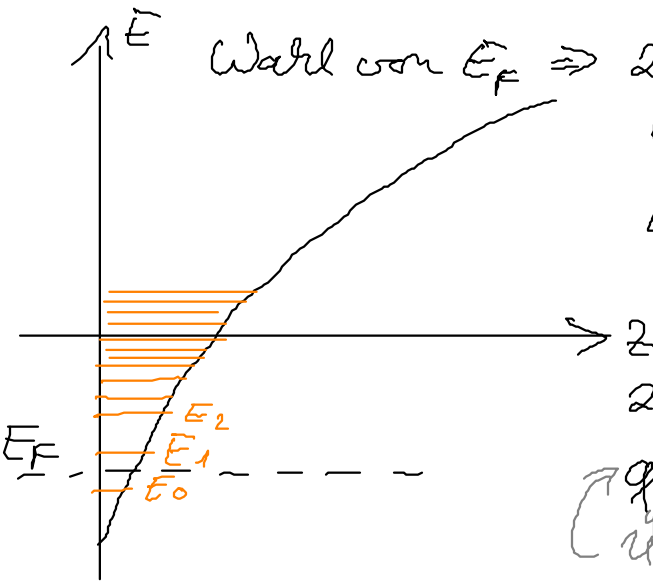
L_ϕ Kohärenzlänge

	direkte Lücke	indirekte Lücke



Donatorminivan Heterostruktur

- Enger Raum (gelb) für Elektronen
- Quantisierung der Energiezustände



Wahl von $E_F \Rightarrow$ 2-dim Problem

$$\psi_u(\mathbf{r}) = \psi_u(z) \exp[i(k_x \cdot x + k_y \cdot y)]$$

$$E(u, k_x, k_y) = -\frac{\hbar^2 (k_x^2 + k_y^2)}{2m} + E_u$$

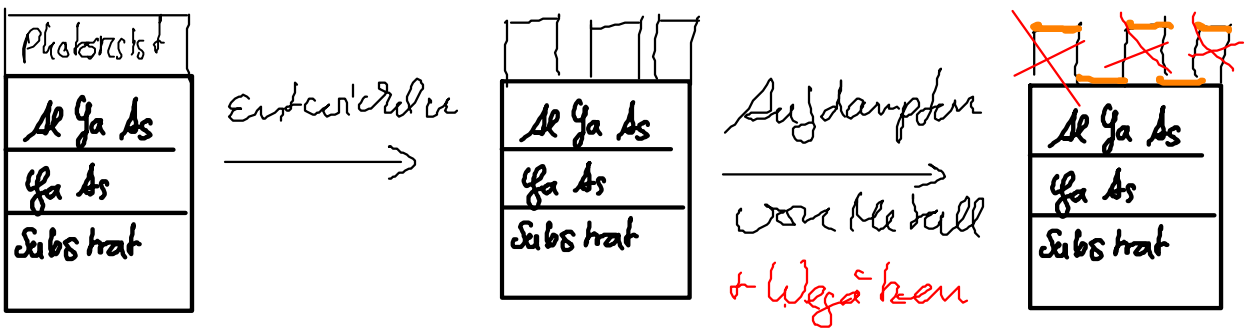
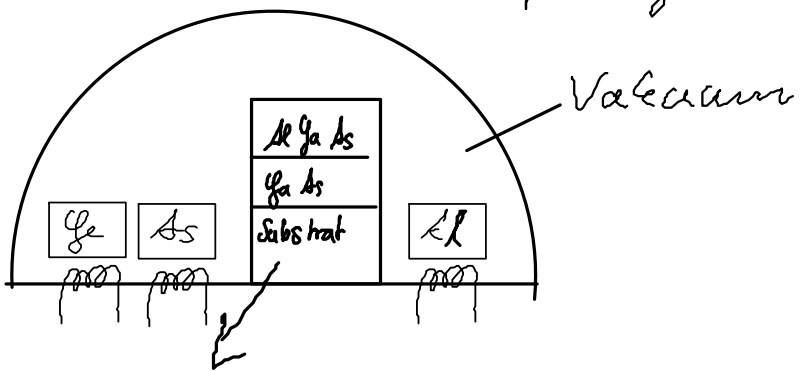
2-dim System: $E_0 \leq E_F \leq E_1$

quasi 2-dim Sys: $E_x \leq E_F$ mit $x \gg \lambda$

Ubergang zum 3-dim System

Herstellung eines Systems (Nanostruktur)

MBF: Nucleas beam epitaxy



Anderer Möglichkeit zur Herstellung von Nanostrukturen

STM = Manipulation ein einzelner Atome ("Scanning tunneling microscope")

1.3 Zustandsdichten

$$E_p = E_0 + \frac{p^2}{2m} \quad (\text{freie Elektronen}) \quad dE = \frac{p}{m} dp \quad E_0 \geq 0$$

Ebene Welle: $\psi(x) = e^{ikx}$ Randbed: $\psi(L) = e^{ikL} = \psi(0)$

$$\Rightarrow kL = 2\pi n \quad k = \frac{2\pi n}{L} \Rightarrow \Delta k = \frac{2\pi}{L}$$

$$3D: \int_{\mathbf{p}} g(E_p) = V \int_{-\infty}^{\infty} \frac{d^3 p}{(2\pi \hbar)^3} g(E_p) = V \frac{4\pi}{(2\pi \hbar)^3} \int_{-\infty}^{\infty} dp p^2 g(E_p)$$

$$= V \int_0^{\infty} dE N^{3D}(E) g(E) \quad g \text{ ist beliebig Funktion von } E$$

$$N^{\text{3d}}(\epsilon) = \frac{m}{2\pi^2 \hbar^3} \sqrt{2m(\epsilon - E_0)} \Theta(\epsilon - E_0)$$

$$N^{\text{1d}}(\epsilon_F) = \frac{m}{2\pi^2 \hbar^3} P_F \hbar, \quad n = \frac{4\pi}{3} P_F^3 \frac{2}{(2\pi \hbar)^3} \leftarrow \text{Spin}$$

QD: $\sum_{\vec{p}} g(\epsilon_p) = A \cdot \int_{-\infty}^{\infty} \frac{d^3p}{(2\pi \hbar)^3} g(\epsilon_p) = \frac{2\pi A}{(2\pi \hbar)^2} \int_0^{\infty} dp p g(\epsilon_p)$

$$= \frac{A}{2\pi \hbar^2} \int_{E_0}^{\infty} \frac{d\epsilon m}{p} p g(\epsilon) = A \int_0^{\infty} \underbrace{\frac{m}{2\pi \hbar^2} \Theta(\epsilon - E_0)}_{N^{\text{3d}}(\epsilon)} g(\epsilon)$$

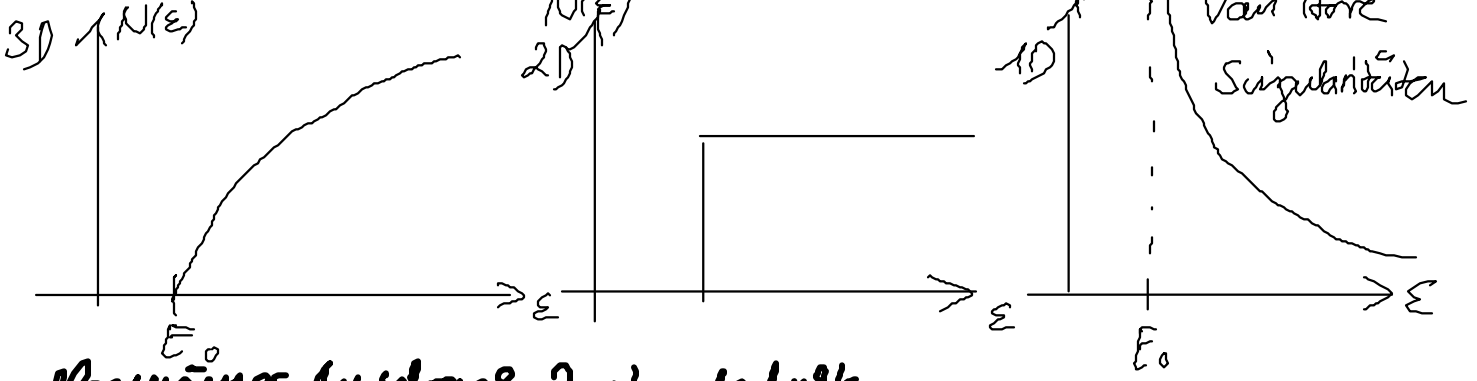
$$= A \int_0^{\infty} d\epsilon N^{\text{3d}}(\epsilon) g(\epsilon)$$

$$N^{\text{2d}}(\epsilon) = \frac{m}{2\pi \hbar^2} \cdot \Theta(\epsilon - E_0), \quad n = 4\pi P_F^2 \frac{2}{(2\pi \hbar)^3} = \frac{2}{\pi \hbar^2} P_F^2$$

1D: $\sum_{\vec{p}} g(\epsilon_p) = L \cdot \int_{-\infty}^{\infty} \frac{dp}{2\pi \hbar} g(\epsilon) = L \int_0^{\infty} d\epsilon N^{\text{1d}}(\epsilon) g(\epsilon)$

$$N^{\text{1d}}(\epsilon) = \frac{2}{2\pi \hbar} \frac{1}{\frac{d\epsilon}{dp}} = \frac{m}{\pi \hbar} \frac{1}{\sqrt{2m\epsilon}}$$

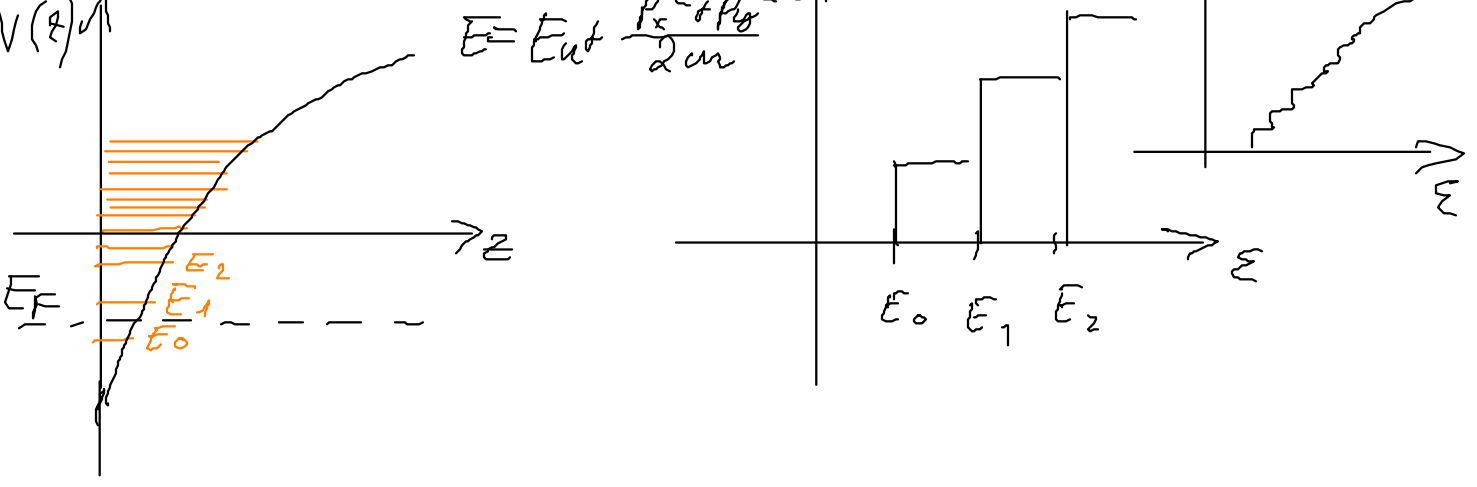
Zustandsdichten:



allgemeiner Ausdruck Zustandsdichte

$$N(\epsilon) = \sum_n \int \frac{d^d k}{(2\pi)^d} \delta(\epsilon - \epsilon_n(\vec{k})) \quad d: \# \text{ Dimensionen}$$

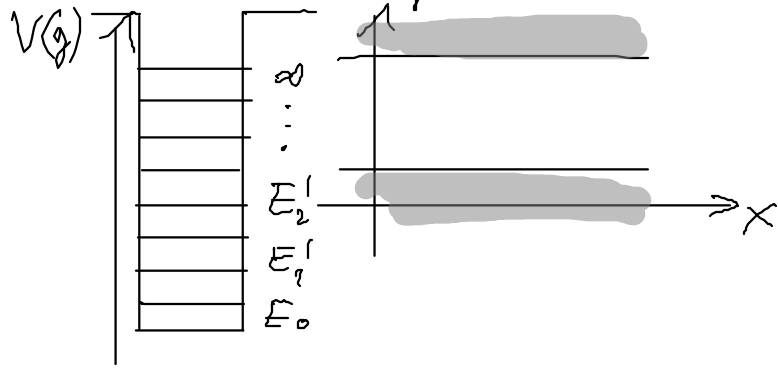
Quasi 2D



Questi 1D

$$\psi(\vec{r}) = \psi_0(z) \chi_n(y) e^{ik_x x}$$

$$E = E_0 + E_n + \frac{\hbar^2 k_x^2}{2m}$$



1.4 Leitfähigkeit

$\vec{j} = \sigma \vec{E}$ ort und zeitunabhängig

$$\vec{j}(\vec{q}, \omega) = \hat{\sigma}(\vec{q}, \omega) \vec{E}(\vec{q}, \omega)$$

Faltungstheorem: $\vec{j}(\omega) = \hat{\sigma}(\omega) \vec{E}(\omega)$

$$\vec{j}(t) = \int \frac{dt''}{\sqrt{2\pi}} \hat{\sigma}(t-t'') \vec{E}(t'')$$

$$\vec{j}(\omega) = \int \frac{d\omega'}{\sqrt{2\pi}} \hat{\sigma}(\omega-\omega') \vec{E}(\omega')$$

$$\hat{\sigma}(\omega) = \int \frac{dt}{\sqrt{2\pi}} \vec{j}(t) e^{-i\omega t}$$

1.4.1 Drude-Leitfähigkeit

$$\vec{j} = ne\vec{v}, \quad l = v \cdot \tau$$

$$\vec{p} = m\vec{v} = e\vec{E} - \frac{m}{\tau}\vec{v}$$

$$\vec{j} = \frac{ne^2\tau}{m} \vec{E}$$

$$\sigma_0 = \frac{ne^2\tau}{m} \text{ (DC Gleichspannung)}$$

$$\hat{\sigma}(\omega) = \frac{ne^2\tau}{m(1+i\omega\tau)} \vec{E}(\omega) \text{ (Wechselsp.)}$$

$$\sigma(\omega) = \frac{ne^2\tau}{m(1+i\omega\tau)}$$

(1 zwischen 2 Schichten)

l : mittlere freie Weglänge

n : Elektronendichte

v : Elektronengeschwindigkeit

1.5 Boltzmann

Verteilungsfkt. $f(\vec{r}, \vec{p}, t)$

μ : chemisches Potential

Gleichgewicht: $f(\vec{r}, \vec{p}) = \frac{1}{\exp[\frac{\epsilon_p - \mu}{k_B T}] + 1}$

$$n(\vec{r}, t) \propto \sum_{\vec{p}} f(\vec{r}, \vec{p}, t)$$

$$\vec{j}(\vec{r}, \vec{p}, t) \propto \sum_{\vec{p}} \vec{v} f(\vec{r}, \vec{p}, t)$$

$$\vec{v} = \vec{v}_p \epsilon_p \text{ (Gruppengeschwindigkeit)}$$

$$\frac{df(\vec{p}, t)}{dt} = \frac{\partial f}{\partial t} + \frac{\partial f}{\partial \vec{r}} \frac{d\vec{r}}{dt} + \frac{\partial f}{\partial \vec{p}} \frac{d\vec{p}}{dt} = \frac{\partial f}{\partial t} + \frac{\vec{p}}{m} \frac{\partial f}{\partial \vec{r}} + \vec{E} \frac{\partial f}{\partial \vec{p}}$$

← Kollisionsterm

$$\left(\frac{\partial}{\partial t} + \frac{\vec{p}}{m} \frac{\partial}{\partial \vec{r}} + e \vec{E} \frac{\partial}{\partial \vec{p}} \right) f = \left(\frac{df}{dt} \right)_{\text{coll}}$$

Boltzmann-Gleichung
 raw - rein Störung

Beispiel: Störstellenstrahlung

$$\left(\frac{\partial f}{\partial t} \right)_{\text{imp}} = -v_F \int d\Omega_{p'} \sigma(\theta_{pp'}) \cdot (f(\vec{p}) - f(\vec{p}')) \Big|_{\epsilon_{p'} = \epsilon_p}$$

$$= -\frac{1}{\tau_{\text{imp}}} f(\vec{p}) + v_{\text{imp}} v_F \int d\Omega_{p'} \cdot \sigma(\theta_{pp'}) f(\vec{p}') \Big|_{\epsilon_p = \epsilon_{p'}}$$

geschw. an Fermi-Sante

$$(\tau_{\text{imp}})^{-1} = v_F \cdot \int d\Omega_{p'} \sigma(\theta_{pp'})$$

S-Wellenstrahlung: $\sigma(\theta) = \text{const}$

$$\left(\frac{\partial f}{\partial t} \right) = -\frac{1}{\tau_{\text{imp}}} (f(\vec{p}) - \langle f(\vec{p}') \rangle), \quad \langle f(\vec{p}') \rangle = \int \frac{d\Omega_{p'}}{4\pi} f(\vec{p}')$$

↑ Relaxationsapproximation